
2SK435

Silicon N-Channel Junction FET

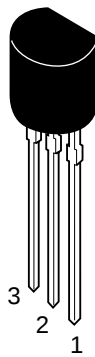
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Application

Low frequency / High frequency amplifier

Outline

TO-92 (2)



- 1. Drain
- 2. Source
- 3. Gate

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	22	V
Gate to source voltage	V_{GSO}	−22	V
Drain current	I_D	100	mA
Gate current	I_G	10	mA
Channel power dissipation	Pch	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

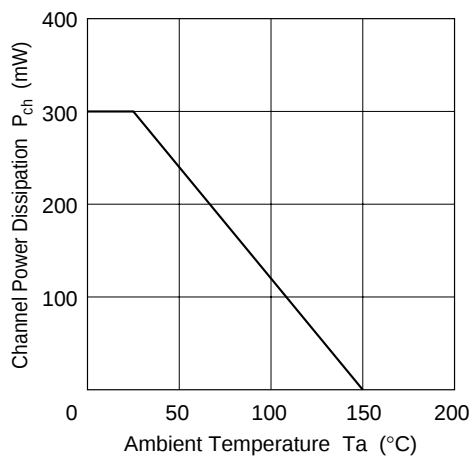
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate to source breakdown voltage	$V_{(BR)GSS}$	−22	—	—	V	$I_G = -10\text{ }\mu\text{A}$, $V_{DS} = 0$
Gate cutoff current	I_{GSS}	—	—	−10	nA	$V_{GS} = -15\text{ V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	—	—	−2.5	V	$V_{DS} = 5\text{ V}$, $I_D = 10\text{ }\mu\text{A}$
Drain current	I_{DSS}^{*1}	6	—	40	mA	$V_{DS} = 5\text{ V}$, $V_{GS} = 0$, Pulse test
Forward transfer admittance	$ y_{fs} $	20	—	—	mS	$V_{DS} = 5\text{ V}$, $I_D = 10\text{ mA}$, $f = 1\text{ kHz}$
Input capacitance	Ciss	—	9.0	11.0	pF	$V_{DS} = 5\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$
Reverse transfer capacitance	Crss	—	2.8	4.0	pF	$V_{DS} = 5\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$
Noise figure	NF	—	0.5	3.0	dB	$V_{DS} = 5\text{ V}$, $I_D = 1\text{ mA}$, $f = 1\text{ kHz}$, $R_g = 1\text{ k}\Omega$

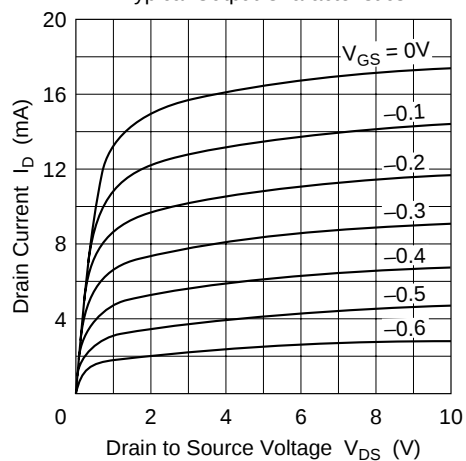
Note: 1. The 2SK435 is grouped by I_{DSS} as follows.

Grade	B	C	D	E
I_{DSS}	6 to 14	12 to 22	18 to 30	26 to 40

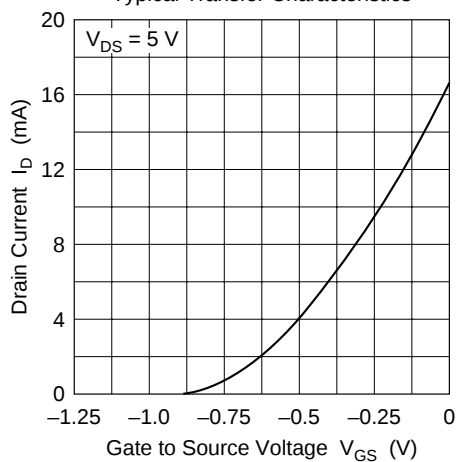
Maximum Channel Dissipation Curve



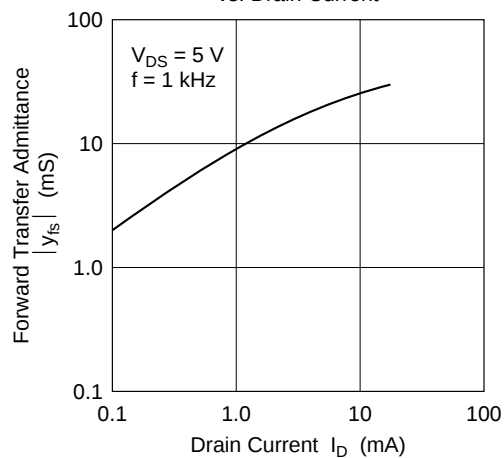
Typical Output Characteristics

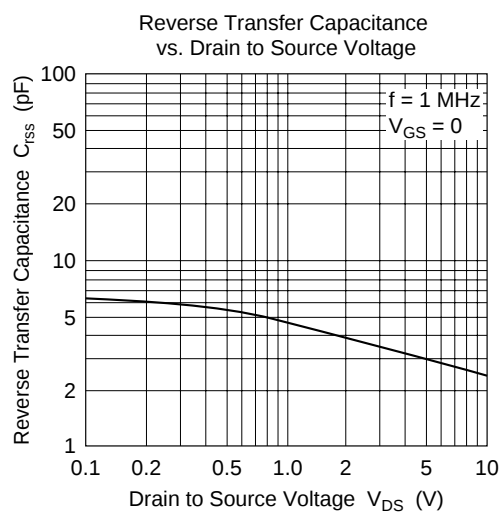
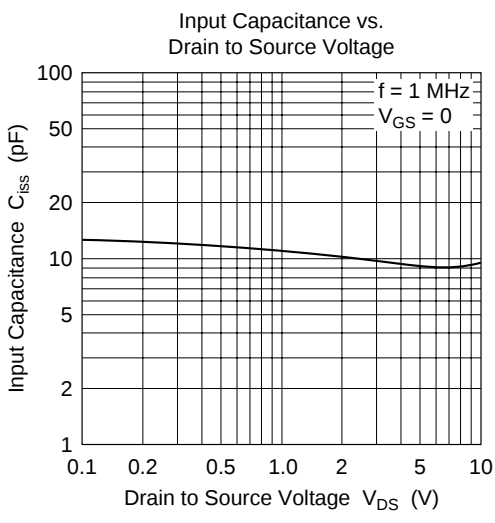
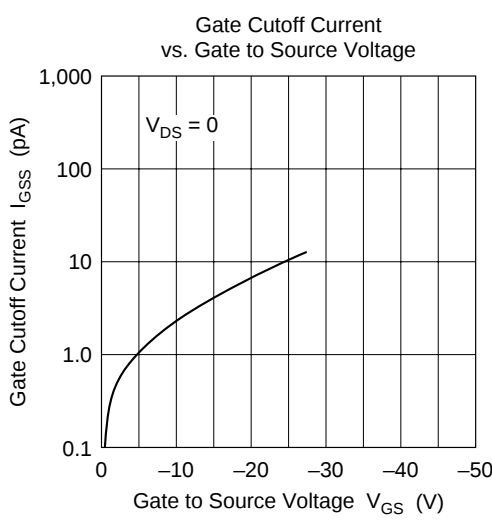
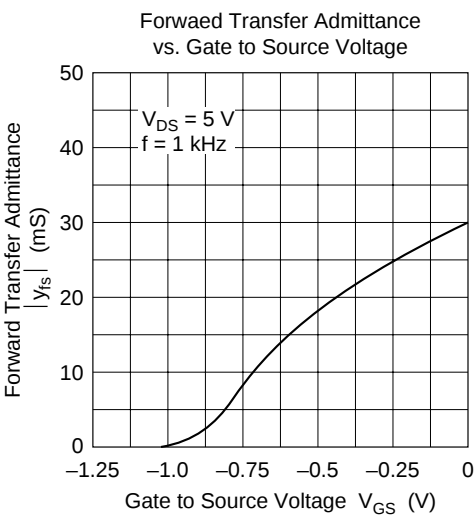


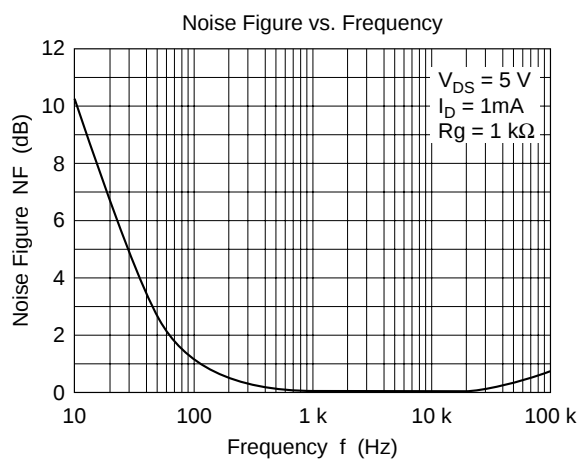
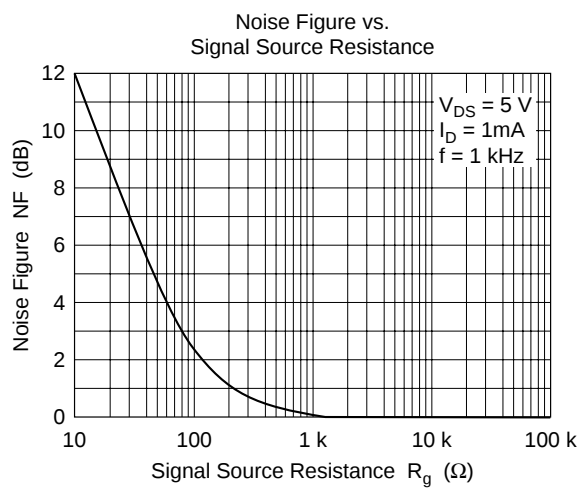
Typical Transfer Characteristics

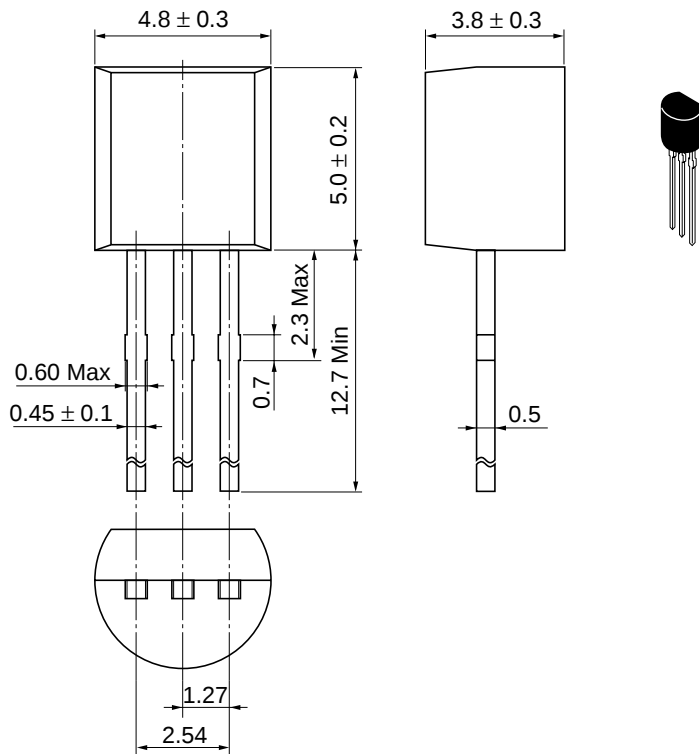


Forward Transfer Admittance vs. Drain Current









Hitachi Code	TO-92 (2)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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